

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16256

DT-33-25



SEMICONDUCTOR

TECHNICAL DATA

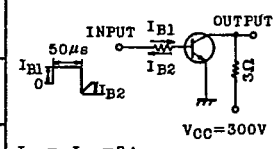
MG100G1FL1

MG100G1AL3

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	600	V
Collector-Emitter Voltage	V _{CE0}	600	V
Collector-Emitter Sustaining Voltage	V _{CE0(SUS)}	450	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	DC I _C	100	A
	1ms I _C	200	
	DC -I _C	100	
Base Current	I _B	5	A
Collector Power Dissipation (Tc=25°C)	P _C	600	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-40~125	°C
Isolation Voltage	V _{isol}	2500 (AC 1 Minute)	V
Screw Torque	-	30	kg·cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =600V, I _E =0	-	-	2.0	mA
Emitter Cut-off Current	I _{EB0}	V _{EB} =6V, I _C =0	-	-	400	mA
Collector-Emitter Sustaining Voltage	V _{CE0(SUS)}	I _C =0.5A, L=40mH	450	-	-	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =100A	100	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100A, I _B =2A	-	-	2.0	V
Base-Emitter Saturation Voltage	V _{BE(sat)}		-	-	2.5	V
Emitter-Collector Voltage	V _{ECO}	I _E =100A, I _B =0	-	-	1.5	V
Reverse Recovery Time	t _{rr}	-I _C =100A, V _{EB} =3V V _{CE} =300V	-	-	2.0	μs
Collector Output Capacitance	C _{ob}	V _{CB} =50V, I _E =0 f=1MHz	-	1000	-	pF
Switching Time	Turn-on Time		-	-	1.0	μs
	Storage Time		-	-	12	
	Fall Time		-	-	2.0	
Thermal Resistance (Junction to Case)	R _{th(j-c)}	Transistor	-	-	0.208	°C/W
		Diode	-	-	0.65	

TOSHIBA CORPORATION

GT1A2A

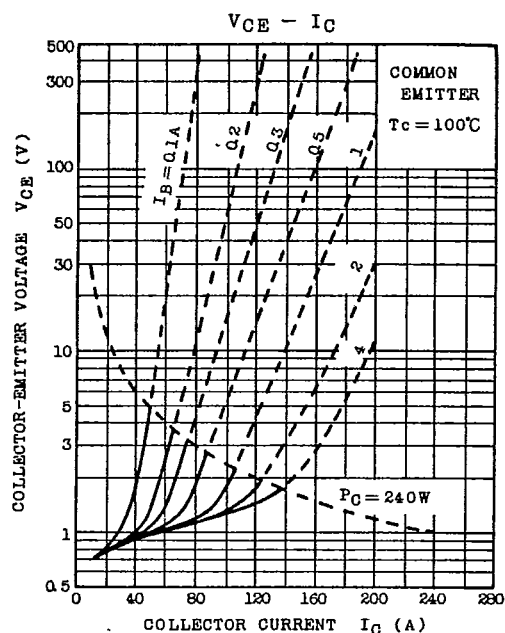


SEMICONDUCTOR

TECHNICAL DATA

MG100G1AL3

MG100G1FL1





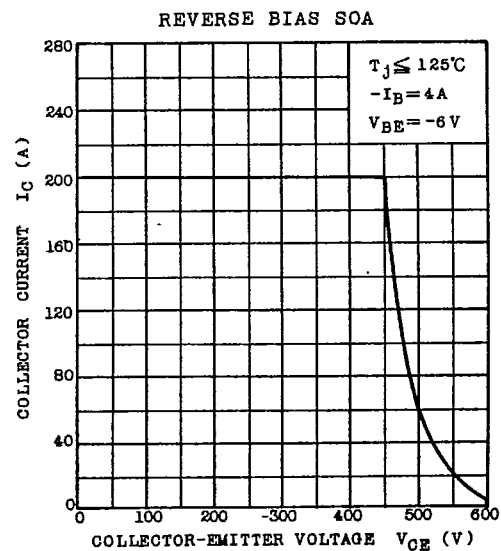
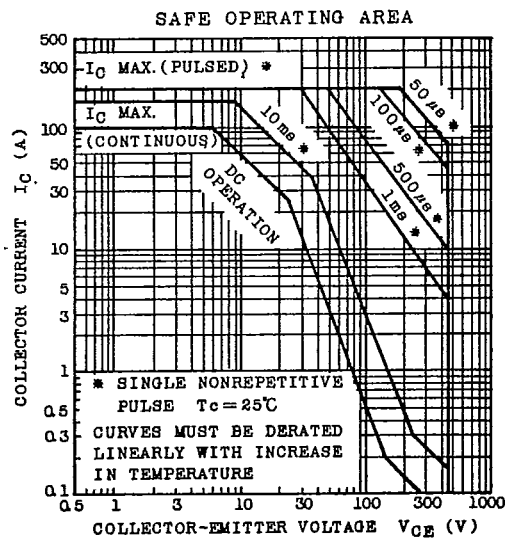
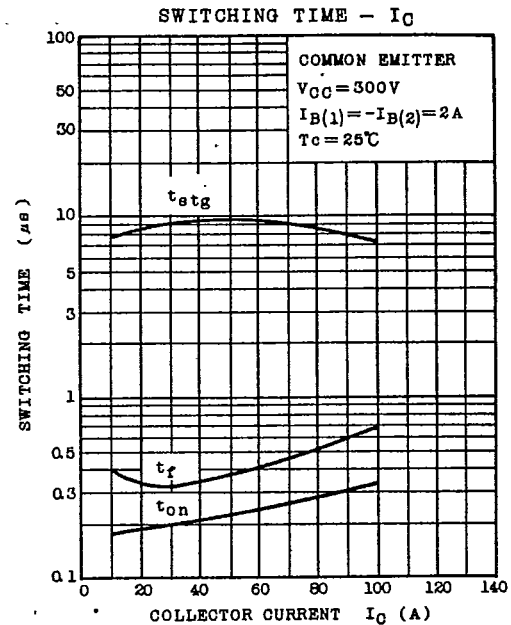
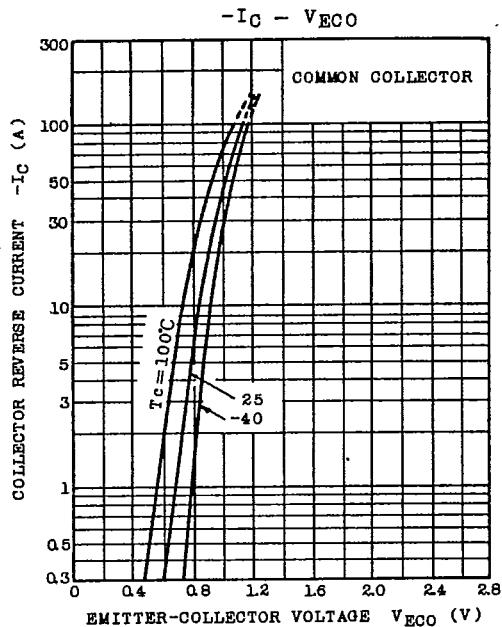
SEMICONDUCTOR

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TECHNICAL DATA

MG100G1AL3

MG100G1FL1



TOSHIBA CORPORATION

GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16259

DT-3335

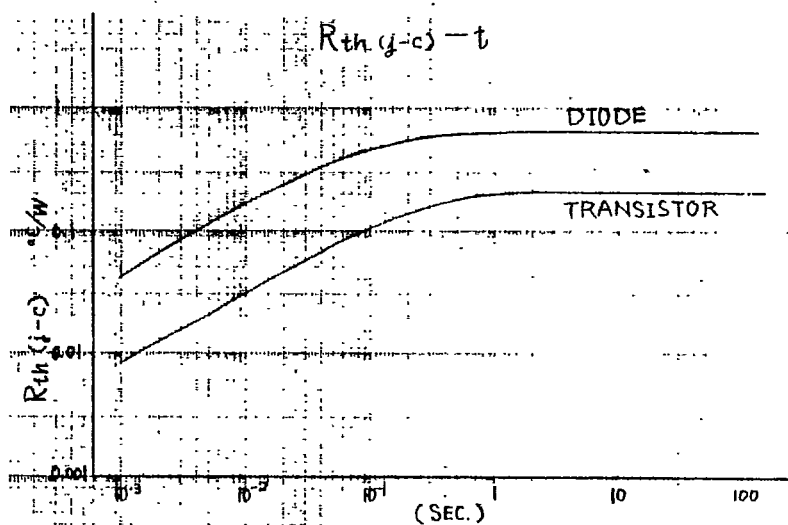
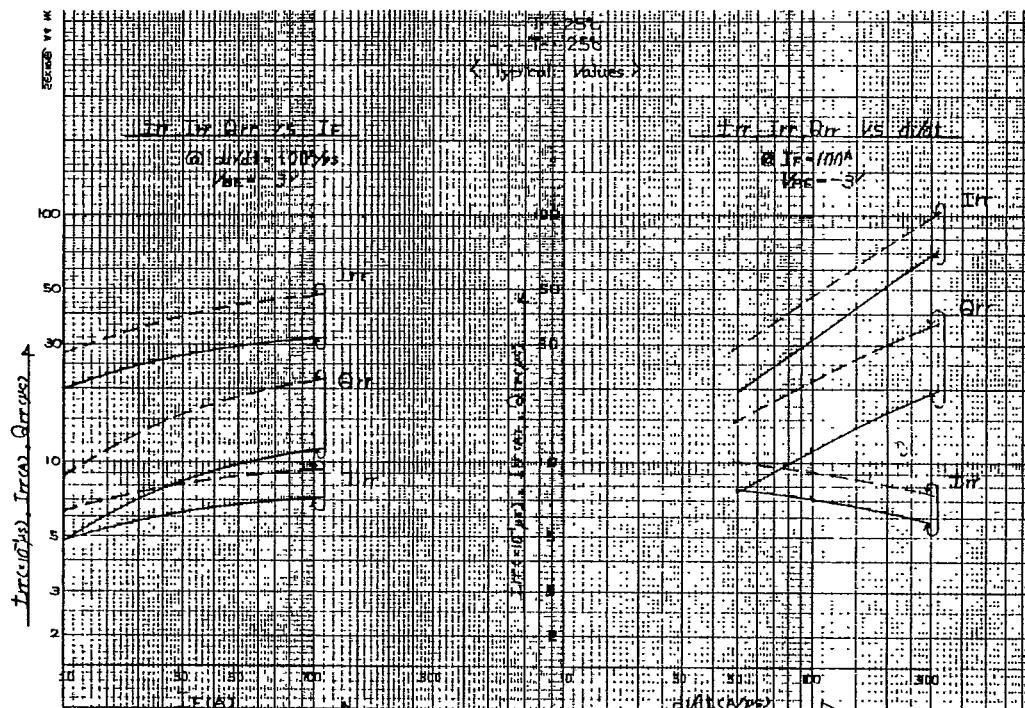


SEMICONDUCTOR

TECHNICAL DATA

MG100G1AL3

MG100G1FL1



TOSHIBA CORPORATION

GT1A2A